

**Radiation Hardened Low Noise Quad Operational Amplifier**

Intersil's Satellite Applications Flow™ (SAF) devices are fully tested and guaranteed to 100kRAD total dose. These QML Class T devices are processed to a standard flow intended to meet the cost and shorter lead-time needs of large volume satellite manufacturers, while maintaining a high level of reliability.

The HS-5104ARH-T is a radiation hardened, monolithic quad operational amplifier that provides highly reliable performance in harsh radiation environments. Its excellent noise characteristics coupled with a unique array of dynamic specifications make this amplifier well-suited for a variety of satellite system applications. Dielectrically isolated, bipolar processing makes this device immune to Single Event Latch-up.

The HS-5104ARH-T shows almost no change in offset voltage after exposure to 100K RAD(Si) gamma radiation, with only a minor increase in current. Complementing these specifications is a post radiation open loop gain in excess of 40K.

This quad operational amplifier is available in an industry standard pinout, allowing for immediate interchangeability with most other quad operational amplifiers.

**Specifications**

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed below must be used when ordering.

**Detailed Electrical Specifications for the HS-5104ARH-T are contained in SMD 5962-95690.** A "hot-link" is provided from our website for downloading.

[www.intersil.com/spacedefense/newsafclasst.asp](http://www.intersil.com/spacedefense/newsafclasst.asp)

Intersil's Quality Management Plan (QM Plan), listing all Class T screening operations, is also available on our website.

[www.intersil.com/quality/manuals.asp](http://www.intersil.com/quality/manuals.asp)

**Ordering Information**

ORDERING NUMBER	PART NUMBER	TEMP. RANGE (°C)
5962R9569001TCC	HS1-5104ARH-T	-55 to 125
HS1-5104ARH/Proto	HS1-5104ARH/Proto	-55 to 125
5962R9569001TXC	HS9-5104ARH-T	-55 to 125
HS9-5104ARH/Proto	HS9-5104ARH/Proto	-55 to 125

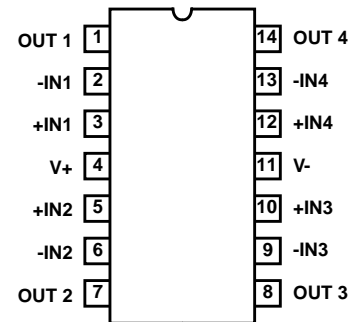
NOTE: **Minimum order quantity for -T is 150 units through distribution, or 450 units direct.**

**Features**

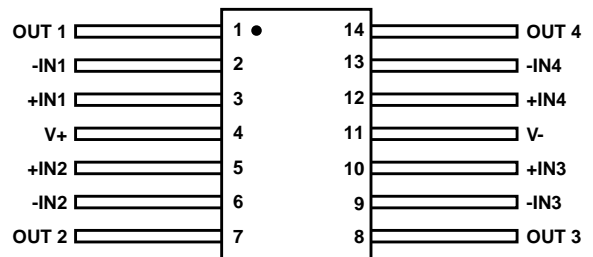
- QML Class T, Per MIL-PRF-38535
- Radiation Performance
  - Gamma Dose ( $\gamma$ )  $1 \times 10^5$  RAD(Si)
  - No Latch-Up, Dielectrically Isolated Device Islands
- Low Noise
  - At 1kHz ..... 4.3nV/ $\sqrt{\text{Hz}}$  (Typ)
  - At 1kHz ..... 0.6pA/ $\sqrt{\text{Hz}}$  (Typ)
- Low Offset Voltage ..... 3.0mV (Max)
- High Slew Rate ..... 2.0V/ $\mu\text{s}$  (Typ)
- Gain Bandwidth Product ..... 8.0MHz (Typ)

**Pinouts**

**HS1-5104ARH-T (SBDIP), CDIP2-T14**  
TOP VIEW



**HS9-5104ARH-T (FLATPACK), CDFF3-F14**  
TOP VIEW



# HS-5104ARH-T

## Die Characteristics

### DIE DIMENSIONS:

(2420 $\mu\text{m}$  x 2530 $\mu\text{m}$  x 483 $\mu\text{m}$   $\pm$ 25.4 $\mu\text{m}$ )  
95 x 99 x 19mils  $\pm$ 1mil

### METALLIZATION:

Type: Al Si Cu  
Thickness: 16.0k $\text{\AA}$   $\pm$ 2k $\text{\AA}$

### SUBSTRATE POTENTIAL:

Unbiased (DI)

### BACKSIDE FINISH:

Silicon

### PASSIVATION:

Type: Nitride ( $\text{Si}_3\text{N}_4$ ) over Silox ( $\text{SiO}_2$ )  
Nitride Thickness: 3.5k $\text{\AA}$   $\pm$ 1.5k $\text{\AA}$   
Silox Thickness: 12.0k $\text{\AA}$   $\pm$ 2k $\text{\AA}$

### WORST CASE CURRENT DENSITY:

< 2.0e5 A/cm<sup>2</sup>

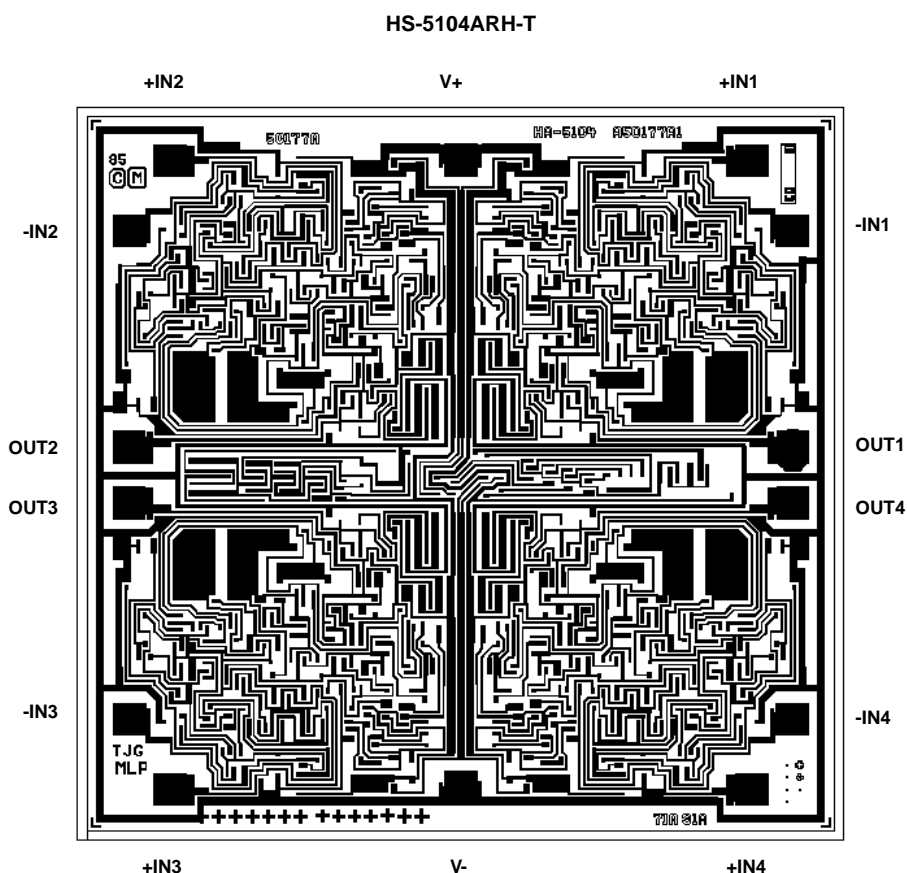
### TRANSISTOR COUNT:

175

### PROCESS:

Bipolar DI

## Metallization Mask Layout



All Intersil semiconductor products are manufactured, assembled and tested under **ISO9000** quality systems certification.

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